

REMARKS

The specification has been amended to correct editorial correction in order to place them in better condition for examination.

Examination on the merits is requested.

Respectfully submitted,



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DRS/sas

VERSION WITH MARKINGS TO SHOW CHANGES MADEIN THE CLAIM:

13. (AMENDED) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising:

a step of growing , on a substrate, a first nitride semiconductor layer including [aluminum and/or] magnesium under a first growth ambient pressure; and ^{and} *under Indirect Co-Cooled*
 a step of growing a second nitride semiconductor layer, which is adjacent to said first nitride semiconductor layer and does not include aluminum and magnesium, under a second growth ambient pressure,

wherein said first growth ambient pressure is lower than said second growth ambient pressure, and is lower than the atmospheric pressure